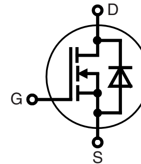
IXYS

IXKP 24N60C5M

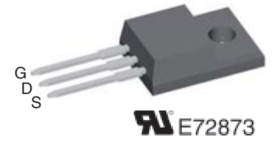
CoolMOS™ 1) Power MOSFET

I_{D25} = 8.5 A
V_{DSS} = 600 V
$R_{DS(on)\,max}$ = 0.165 Ω

Fully isolated package
N-Channel Enhancement Mode
Low R_{DSon}, High V_{DSS} MOSFET
Ultra low gate charge



TO-220 FP



Preliminary data

MOSFET			
Symbol	**Conditions**	**Maximum Ratings**	
V_{DSS}	T_{VJ} = 25°C	600	V
V_{GS}		± 20	V
I_{D25} I_{D90}	T_C = 25°C T_C = 90°C	8.5 6.0	A A
E_{AS} E_{AR}	single pulse repetitive } I_D = 7.9 A; T_C = 25°C	522 0.79	mJ mJ
dV/dt	MOSFET dV/dt ruggedness V_{DS} = 0...480 V	50	V/ns

Symbol	**Conditions**	**Characteristic Values** (T_{VJ} = 25°C, unless otherwise specified)			
		min.	**typ.**	**max.**	
R_{DSon}	V_{GS} = 10 V; I_D = 10 A		150	165	mΩ
$V_{GS(th)}$	V_{DS} = V_{GS}; I_D = 0.79 mA	2.5	3	3.5	V
I_{DSS}	V_{DS} = 600 V; V_{GS} = 0 V T_{VJ} = 25°C T_{VJ} = 125°C		 10	1	µA µA
I_{GSS}	V_{GS} = ± 20 V; V_{DS} = 0 V			100	nA
C_{iss} C_{oss}	V_{GS} = 0 V; V_{DS} = 100 V f = 1 MHz		2000 100		pF pF
Q_g Q_{gs} Q_{gd}	V_{GS} = 0 to 10 V; V_{DS} = 400 V; I_D = 12 A		40 9 13	52	nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	V_{GS} = 10 V; V_{DS} = 400 V I_D = 12 A; R_G = 3.3 Ω		12 5 50 5		ns ns ns ns
R_{thJC}				3.65	K/W

Features

- fast CoolMOS™ 1) power MOSFET 4th generation
  - High blocking capability
  - Lowest resistance
  - Avalanche rated for unclamped inductive switching (UIS)
  - Low thermal resistance due to reduced chip thickness
- Enhanced total power density

Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)
- Welding
- Inductive heating
- PDP and LCD adapter

1) CoolMOS™ is a trademark of Infineon Technologies AG.

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20090209d

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Source-Drain Diode

Symbol	Conditions	min.	typ.	max.	
	(T_{VJ} = 25°C, unless otherwise specified)				
I_S	V_{GS} = 0 V			12	A
V_{SD}	I_F = 12 A; V_{GS} = 0 V		0.9	1.2	V
t_{rr}	I_F = 12 A; $-di_F/dt$ = 100 A/μs; V_R = 400 V		390		ns
Q_{RM}			7.5		μC
I_{RM}			38		A

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-55...+150	°C
T_{stg}		-55...+150	°C
M_d	mounting torque	0.4 ... 0.6	Nm

Symbol	Conditions	min.	typ.	max.	
R_{thCH}	with heatsink compound		0.50		K/W
R_{thJA}	thermal resistane juntion - ambient		80		K/W
Weight			2		g

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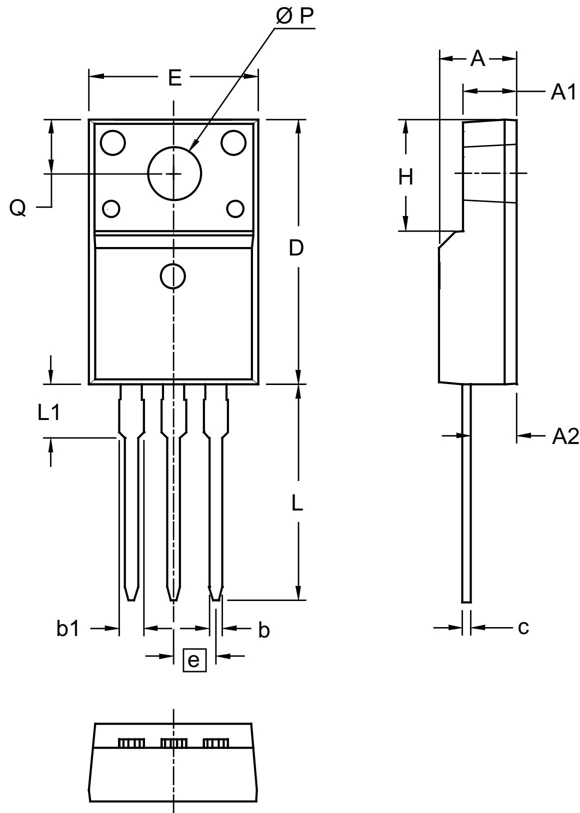
TO-220 ABFP Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

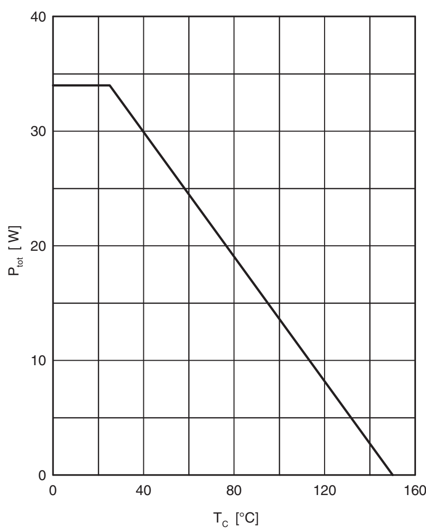


Fig. 1 Power dissipation

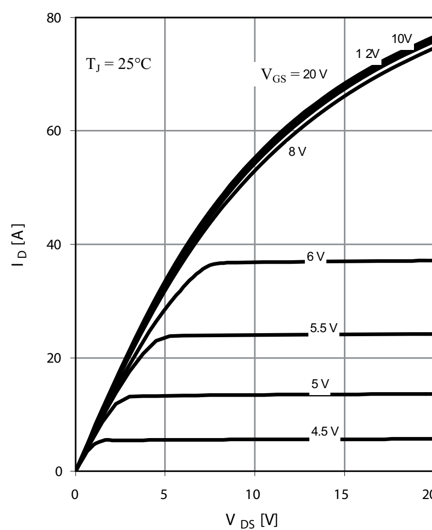


Fig. 2 Typ. output characteristics

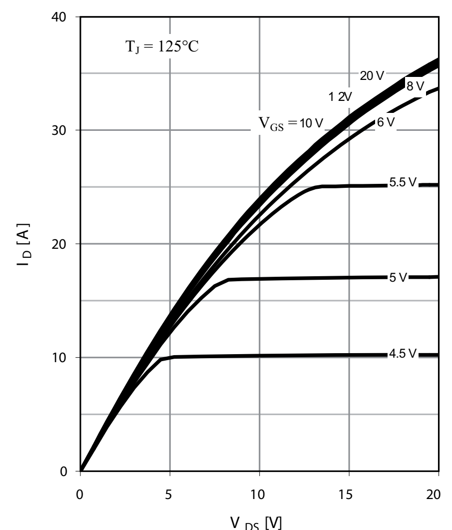


Fig. 3 Typ. output characteristics

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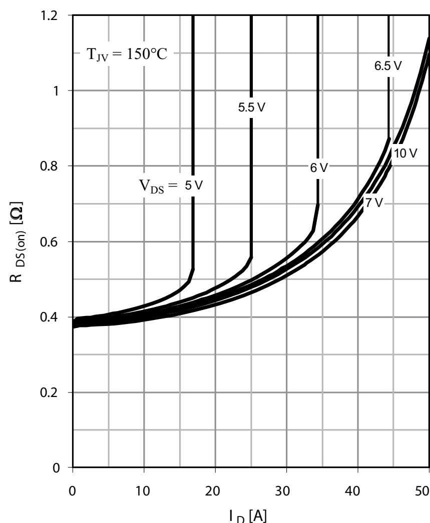

Fig. 4 Typ. drain-source on-state resistance characteristics of IGBT

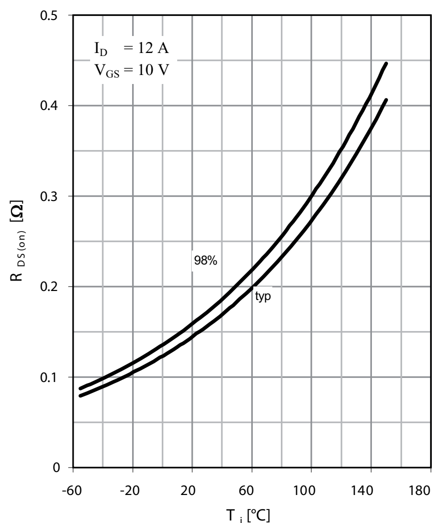

Fig. 5 Drain-source on-state resistance

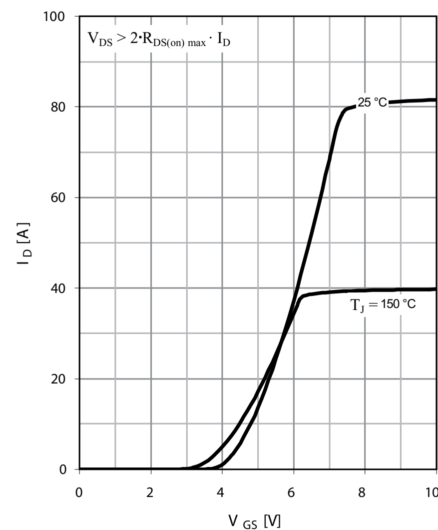

Fig. 6 Typ. transfer characteristics

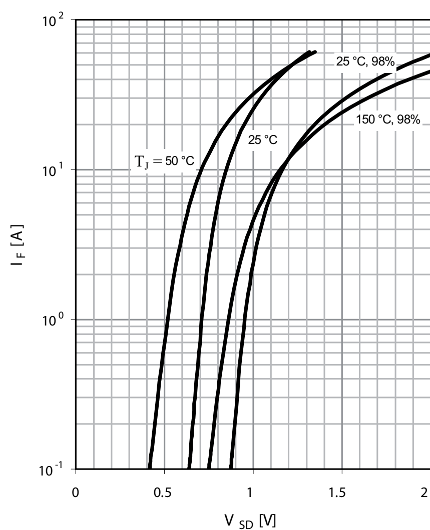

Fig. 7 Forward characteristic of reverse diode

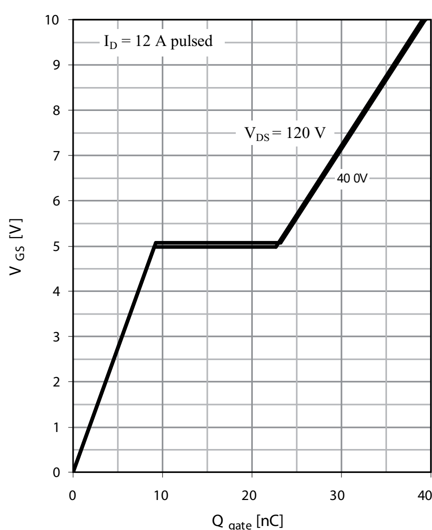

Fig. 8 Typ. gate charge

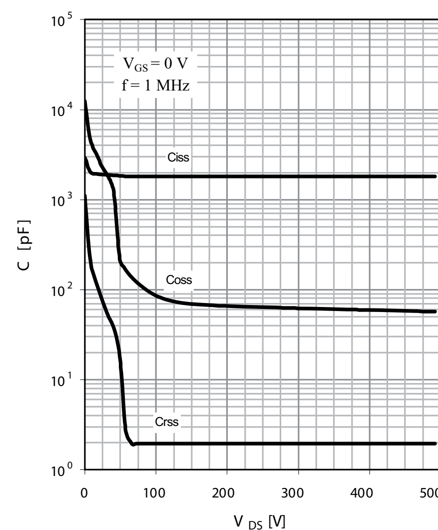

Fig. 9 Typ. capacitances

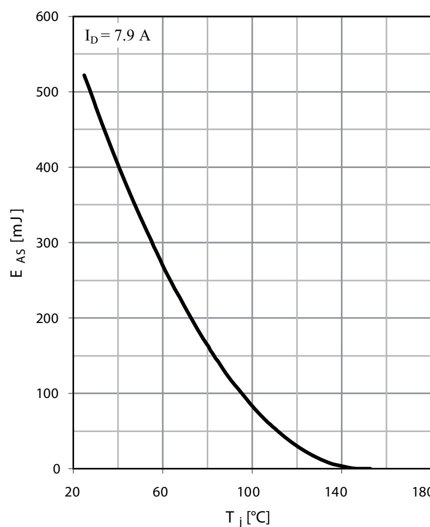

Fig. 10 Avalanche energy

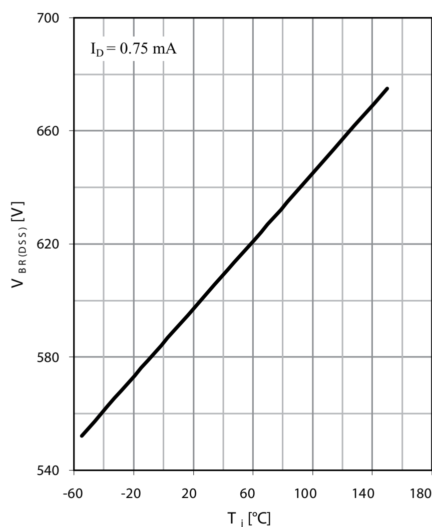

Fig. 11 Drain-source breakdown voltage

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